

## 2N1595-2N1599

### SILICON THYRISTORS

High-reliability discrete products and engineering services since 1977

#### FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

Symbol	Ratings	2N1595	2N1596	2N1597	2N1598	2N1599	Unit
V <sub>RSM(REP)</sub>	Peak reverse blocking voltage*	50	100	200	300	400	V
I <sub>T(RMS)</sub>	Forward current RMS (all conduction angles)	1.6					
I <sub>TSM</sub>	Peak surge current (one-cycle, 60Hz, T <sub>J</sub> = -65 to +125°C)	15					
$P_{GM}$	Peak gate power – forward	0.1					
P <sub>G(AV)</sub>	Average gate power – forward	0.01					
I <sub>GM</sub>	Peak gate current – forward	0.1					
$V_{GFM}$	Peak gate voltage – forward	10					
$V_{\text{GRM}}$	Peak gate voltage – reverse	10					V
TJ	Operating junction temperature range	-65 to +125					°C
T <sub>STG</sub>	Storage temperature range	-65 to +150					°C

#### MAXIMUM RATINGS

\*V<sub>DRM</sub> or V<sub>RSM</sub> can be applied for all types on a continuous dc basis without incurring damage.

#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise specified)

Symbol	Ratings		2N1595	2N1596	2N1597	2N1598	2N1599	Unit	
V <sub>DRM</sub>	Peak forward blocking voltage*	Min.	50	100	200	300	400	V	
I <sub>rrm</sub>	Peak reverse blocking current (Rated V <sub>DRM</sub> , T <sub>J</sub> = 125°C)	Max.	1.0			mA			
I <sub>DRM</sub>	Peak forward blocking current (Rated $V_{DRM}$ with gate open, $T_J$ = 125°C)	Max.	1.0			mA			
	Gate trigger current	Тур.	2.0				mA		
I <sub>GT</sub>	Anode voltage = 7.0 Vdc, $R_L = 12\Omega$	Max.			10				
	Gate trigger voltage	Тур.		0.7					
V <sub>GT</sub>	Anode voltage = 7.0Vdc, $R_L = 12\Omega$	Max.	Max. 3.0				v		
	$V_{DRM}$ = rated, $R_L$ = 100 $\Omega$ , $T_J$ = 125°C	Min.			0.2				
I <sub>H</sub>	Holding current Anode voltage = 7.0 Vdc, gate open	Тур.	5.0			mA			
N/	Forward on-voltage	Тур.			1.1			V	
V <sub>TM</sub>	I <sub>T</sub> = 1Adc	Max.			2.0			V	
t <sub>gt</sub>	Turn-on time $(t_d+t_r)$ I <sub>GT</sub> = 10mA, I <sub>T</sub> = 1A	Тур.	0.8		μs				
tq	Turn-off time $I_T = 1A$ , $I_R = 1A$ , $dv/dt = 20 V/\mu s$ , $T_J = 125^{\circ}C$ $V_{DRM} = rated voltage$	Тур.			10			μs	

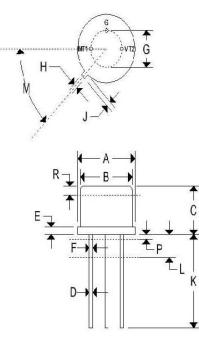
 $V_{DRM}$  or  $V_{RSM}$  can be applied for all types on a continuous dc basis without incurring damage.



High-reliability discrete products and engineering services since 1977

#### MECHANICAL CHARACTERISTICS

Case:	ТО-39
Marking:	Body painted, alpha-numeric
Pin out:	See below



	TO-39					
	Inc	hes	Millimeters			
	Min	Max	Min	Max		
A	0.335	0.370	8.510	9.390		
В	0.305	0.335	7.750	8.500		
С	0.240	0.260	6.100	6.600		
D	0.016	0.021	0.410	0.530		
E	0.009	0.041	0.230	1.040		
F	0.016	0.019	0.410	0.480		
G	0.200 BSC		5.080 BSC			
Η	0.028	0.034	0.720	0.860		
J	0.029	0.045	0.740	1.140		
K	0.500	0.750	12.700	19.050		
L	0.250	171	6.350	151		
М	45°C BSC		45°C BSC			
Р		0.050	8 <b>7</b> 8	1.270		
R	0.100		2.540	121		

# 2N1595-2N1599

### SILICON THYRISTORS